

isc Silicon PNP Power Transistor

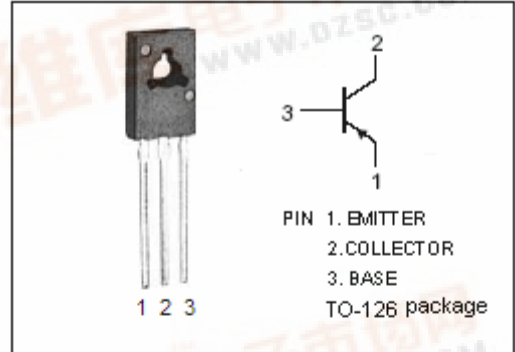
2SA715

DESCRIPTION

- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -35V$ (Min)
- Complement to Type 2SC1162

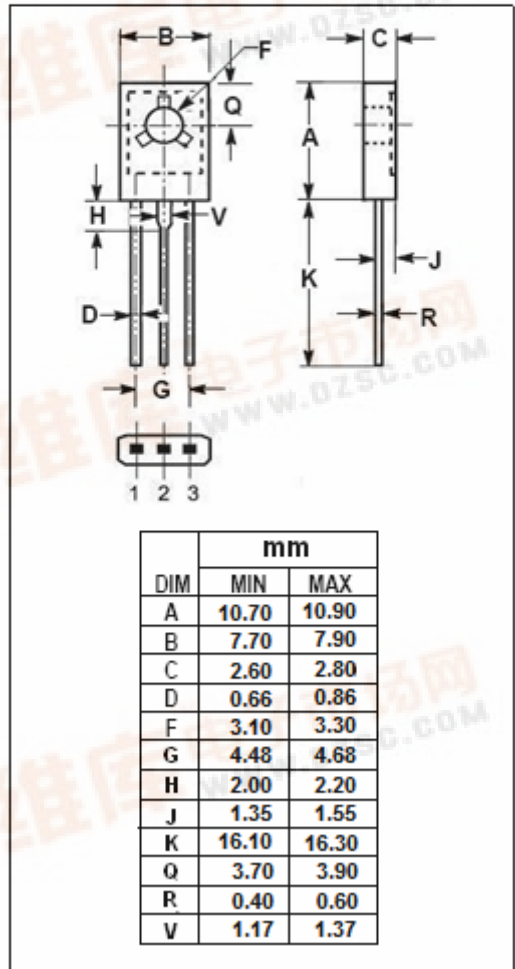
APPLICATIONS

- Designed for use in low frequency power amplifier applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-35	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-2.5	A
I_{CM}	Collector Current-Peak	-3.0	A
P_C	Collector Power Dissipation @ $T_a=25^\circ C$	0.75	W
	Total Power Dissipation @ $T_C=25^\circ C$	10	
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1\text{mA}; I_E = 0$	-35			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; R_{BE} = \infty$	-35			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -1.5\text{A}; V_{CE} = -2\text{V}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -35\text{V}; I_E = 0$			-20	μA
h_{FE-1}	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -2\text{V}$	60		320	
h_{FE-2}	DC Current Gain	$I_C = -1.5\text{A}; V_{CE} = -2\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.2\text{A}; V_{CE} = -2\text{V}$		160		MHz

◆ h_{FE-1} Classifications

B	C	D
60-120	100-200	160-320